

K. Memory (Design & Process Technology) 분과

2020년 2월 14일(금), 15:45-17:30 / Room G (스페이스 II+III, 6층)

■ [FG3-K] Emerging Memory III

좌장: 김성준 교수 (충북대학교), 김형진 교수 (영남대학교)

FG3-K-1 15:45-16:15	[초청] Principle, Materials, Process and Applications of Hafnia Ferroelectric Tunnel Junction Device Sanghun Jeon <i>School of Electrical Engineering, KAIST</i>
FG3-K-2 16:15-16:45	[초청] CMOS Compatible Silicon Nitride Resistive Switching Memory Sungjun Kim <i>School of Electronics Engineering, Chungbuk National University</i>
FG3-K-3 16:45-17:00	Improved Switching Speed Characteristics of Ag-doped HfO₂ Atomic Switch Devices Seongjae Heo, Jaehyuk Park, Jongmyung Yoo, Seokjae Lim, Sangmin Lee, and Hyunsang Hwang <i>Center for Single Atom-based Semiconductor Device and also Department of Materials Science and Engineering, POSTECH</i>
FG3-K-4 17:00-17:15	Electric Characteristics Of Z²-FET with Positive Feedback Mechanism Sehyun Kwon ¹ , Yong Tae Kim ² , and Jinho Ahn ¹ ¹ Hanyang University, ² KIST
FG3-K-5 17:15-17:30	열/전기 모델과 상장 모델의 통합 해석을 통한 상변화메모리의 Reset Pulse Falling Time에 따른 재결정화도 연구 이환욱, 권용우 <i>홍익대학교 신소재공학과</i>